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November 2013

### **FDPF15N65**

# N-Channel UniFET<sup>TM</sup> MOSFET 650 V, 15 A, 440 m $\Omega$

#### **Features**

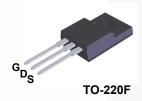
- $R_{DS(on)}$  = 360 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 7.5 A
- Low Gate Charge (Typ. 48.5 nC)
- Low C<sub>rss</sub> (Typ. 23.6 pF)
- · 100% Avalanche Tested

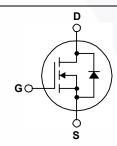
## **Applications**

- · LCD/LED/PDP TV and Monitor
- Uninterruptible Power Supply

## **Description**

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter	FDPF15N65	Unit
V <sub>DSS</sub>	Drain-Source Voltage		650	V
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	15* 9.5*	A A
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	60*	А
V <sub>GSS</sub>	Gate-Source voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		637	mJ
I <sub>AR</sub>	Avalanche Current (Note 1		15	А
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		25.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C) - Derate Above 25°C	38.5 0.3	W W/°C
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storag	e Temperature Range	-55 to +150	°C
TL	Maximum Lead Temp	perature for Soldering, 1/8" from Case for 5 Seconds	300	°C

<sup>\*</sup> Drain current limited by maximum junction termperature.

#### **Thermal Characteristics**

Symbol	Parameter	FDPF15N65	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	C/VV

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF15N65	FDPF15N65	TO-220F	Tube	N/A	N/A	50 units

## $\textbf{Electrical Characteristics} \quad \textbf{T}_{C} = 25^{\circ} \text{C unless otherwise noted}.$

Symbol	Parameter	Conditions		Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_J = 25^{\circ}\text{C}$	650			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.65		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 520 V, T <sub>C</sub> = 125°C			1 10	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Charac	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.5 A		0.36	0.44	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 7.5 A		19.2		S
Dynamic C	Characteristics					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		2380	3095	pF
C <sub>oss</sub>	Output Capacitance			295	385	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			23.6	35.5	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time $V_{DD} = 325 \text{ V}, I_D = 15 \text{ A},$			65	140	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS}$ = 10 V, $R_G$ = 21.7 $\Omega$ (Note 4)		125	260	ns
$t_{d(off)}$	Turn-Off Delay Time			105	220	ns
t <sub>f</sub>	Turn-Off Fall Time			65	140	ns
$Q_g$	Total Gate Charge	$V_{DS} = 520 \text{ V}, I_{D} = 15 \text{ A},$		48.5	63.0	nC
$Q_{gs}$	Gate-Source Charge V <sub>GS</sub> = 10 V		/	14.0		nC
$Q_{gd}$	Gate-Drain Charge	(Note 4)		21.2		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				15*	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				60	Α
$V_{SD}$	Drain-Source Diode Forward Voltage V <sub>GS</sub> = 0 V, I <sub>S</sub> = 15 A				1.4	V
t <sub>rr</sub>	Reverse Recovery Time			496		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> /dt =100 A/μs		5.69		μC

#### Notes:

<sup>1.</sup> Repetitive rating: pulse-width limited by maximum junction temperature.

<sup>2.</sup> L = 5.23 mH, I  $_{AS}$  = 15 A, V  $_{DD}$  = 50 V, R  $_{G}$  = 25  $\Omega,$  starting T  $_{J}$  = 25  $^{\circ}C.$ 

<sup>3.</sup> I<sub>SD</sub>  $\leq$  15 A, di/dt  $\leq$  200 A/ $\mu$ s, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C.

<sup>4.</sup> Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

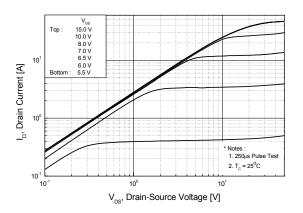


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

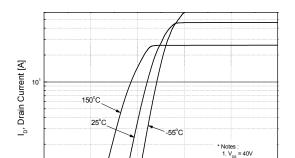


Figure 2. Transfer Characteristics

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

V<sub>GS</sub>, Gate-Source Voltage [V]

2. 250us Pulse Test

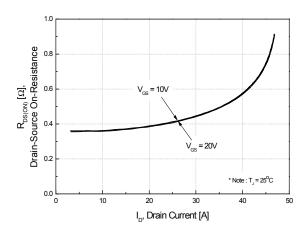
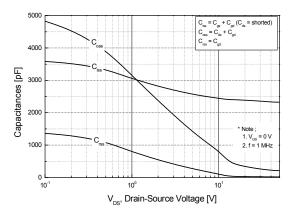


Figure 5. Capacitance Characteristics

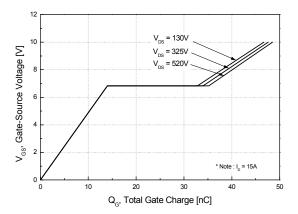


Notes:

10°
0.2
0.4
0.6
0.8
1.0
1.2
1.4

V<sub>SD</sub>, Source-Drain voltage [V]

Figure 6. Gate Charge Characteristics



## **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

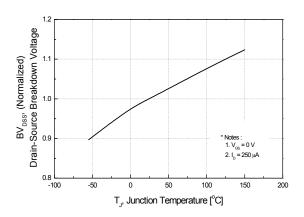


Figure 8. On-Resistance Variation vs. Temperature

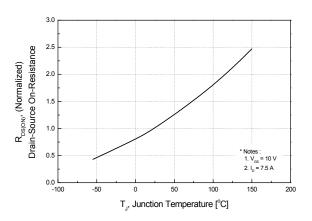
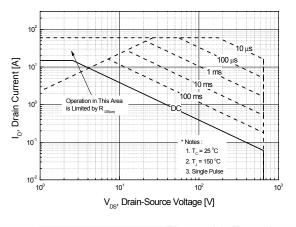


Figure 9. Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature



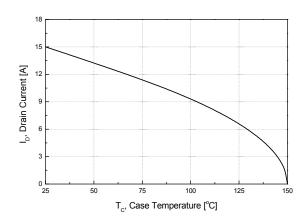
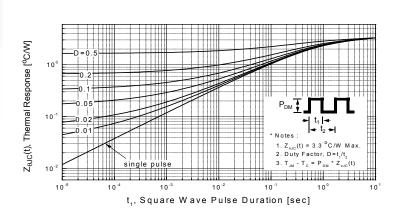


Figure 11. Transient Thermal Response Curve



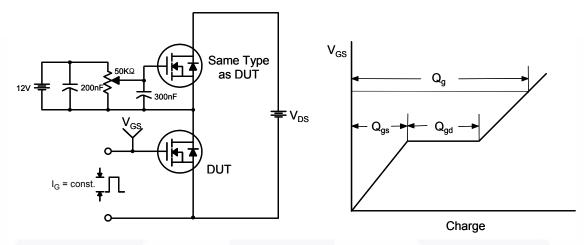


Figure 12. Gate Charge Test Circuit & Waveform

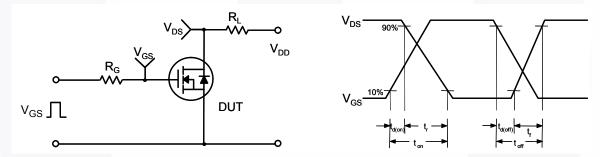


Figure 13. Resistive Switching Test Circuit & Waveforms

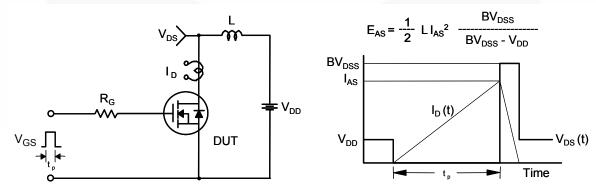


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

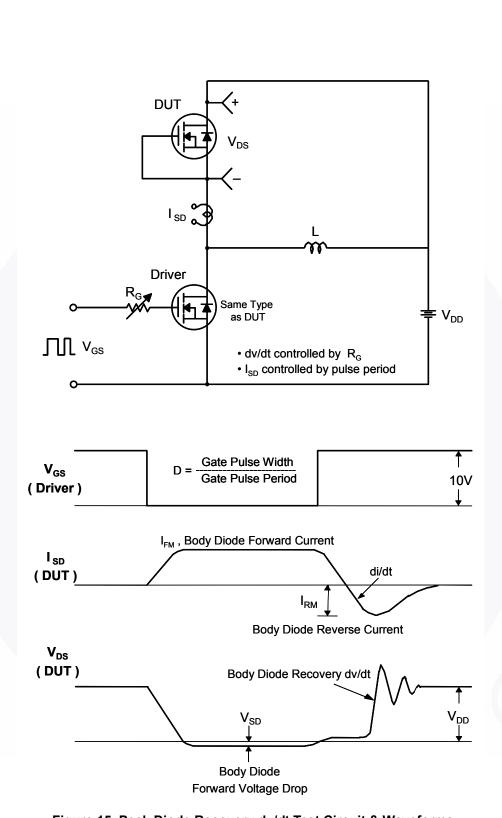


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

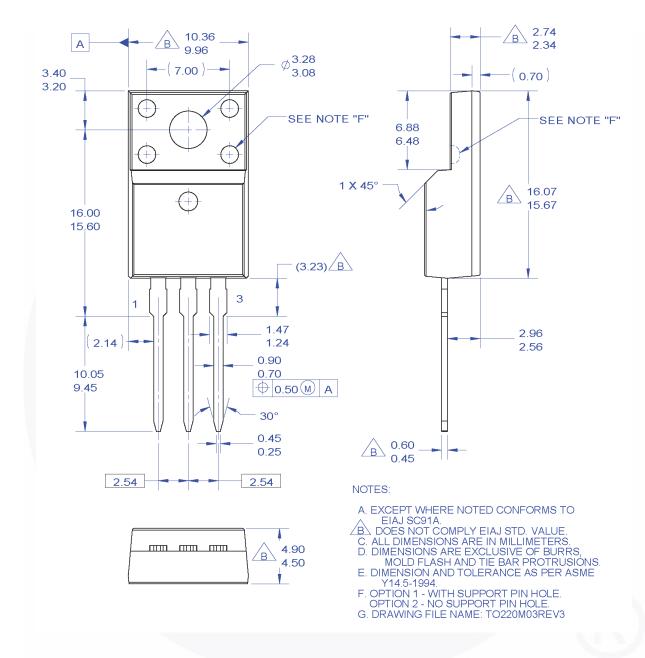


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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